

# *Understanding the Selective Area Nucleation and Growth of GaN nanocolumns by MBE using Ti nanomasks*

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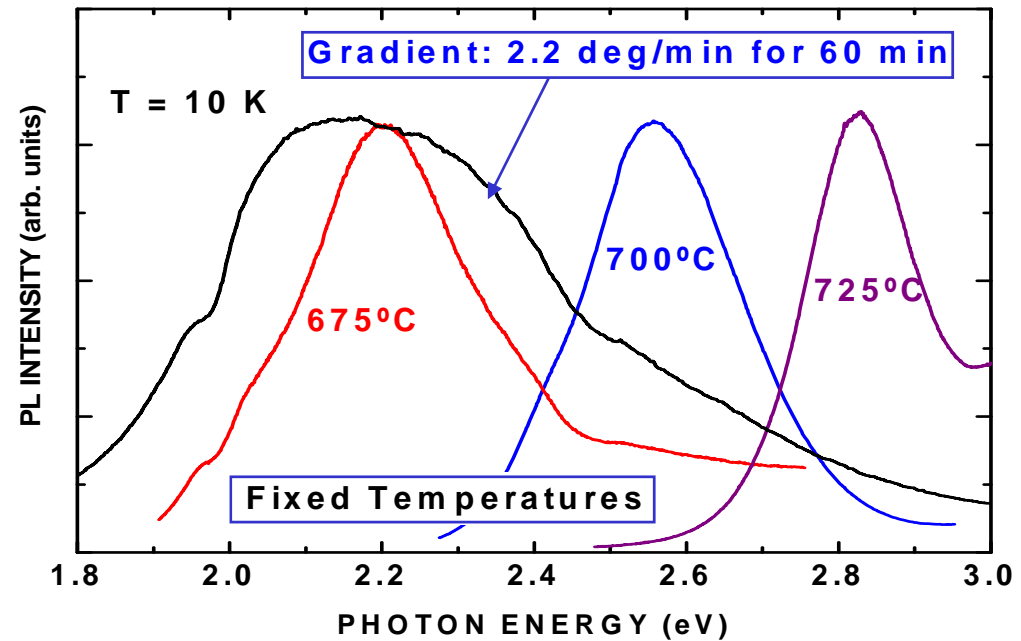
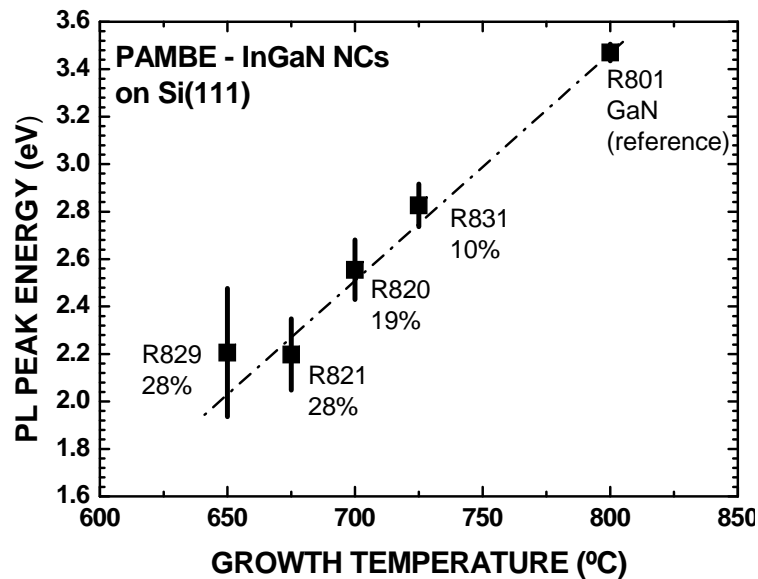
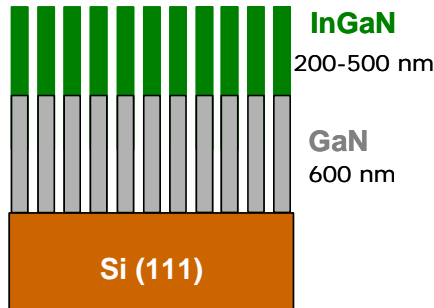
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- Self- assembled Ga(In)N Nanorods and Nanostructures
- Ordered growth of GaN Nanorods: masks issues
- Ordered growth of GaN Nanorods: mechanisms
- White NanoLEDs

## Single and graded composition InGaN NCs with broad emission



temperature gradient: 750 to 650°C (In% from 2 to 30%)